

**isc Silicon NPN Power Transistor**
**2SC3212**
**DESCRIPTION**

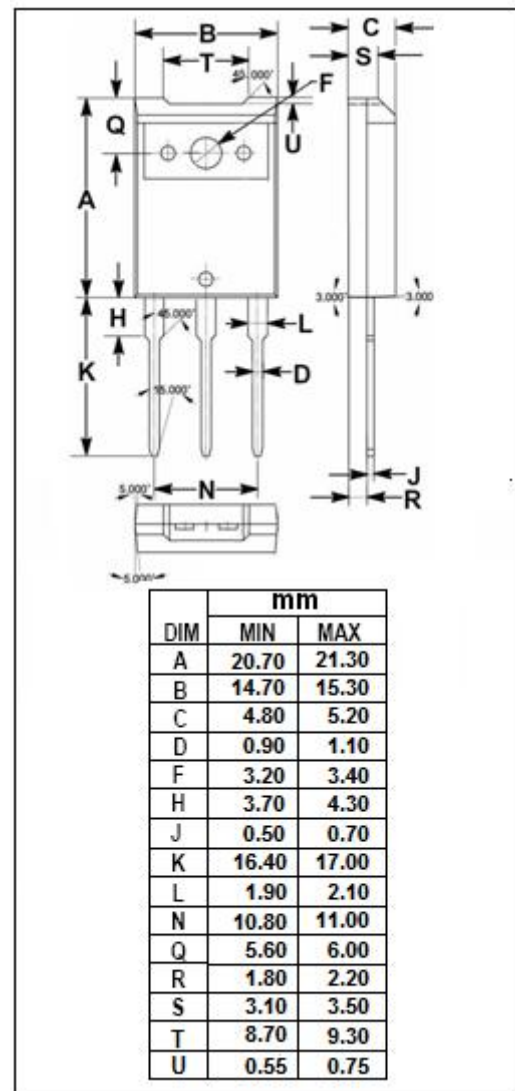
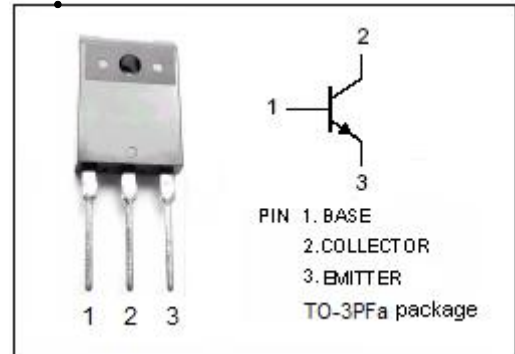
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 500V(\text{Min.})$
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = 1.0V(\text{Max.}) @ I_C = 5A$
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for high speed switching applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	800	V
$V_{CEO}$	Collector-Emitter Voltage	500	V
$V_{EBO}$	Emitter-Base Voltage	8	V
$I_C$	Collector Current-Continuous	7	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current-Continuous	4	A
$P_C$	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	3	W
	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	100	
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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**ELECTRICAL CHARACTERISTICS**
**T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> =0	500			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	15			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	8			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		3.5		MHz

Switching Times; Resistive Load

t <sub>on</sub>	Turn-on Time				1.0	μs
t <sub>s</sub>	Storage Time	I <sub>C</sub> = 5A; I <sub>B1</sub> = -I <sub>B2</sub> = 1A; V <sub>CC</sub> = 200V			2.5	μs
t <sub>f</sub>	Fall Time				1.0	μs

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